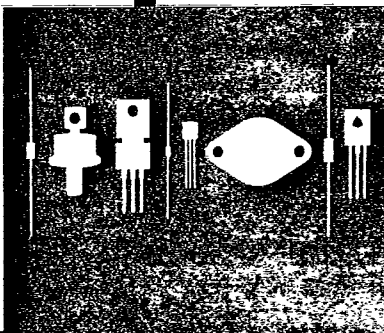


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145 Adams Avenue
Hauppauge, New York 11788



1N5550
1N5551
1N5552
1N5553
1N5554

GLASS PASSIVATED RECTIFIER
3.0 AMPS, 200 THRU 1000 VOLTS

GPR-3A CASE

DESCRIPTION

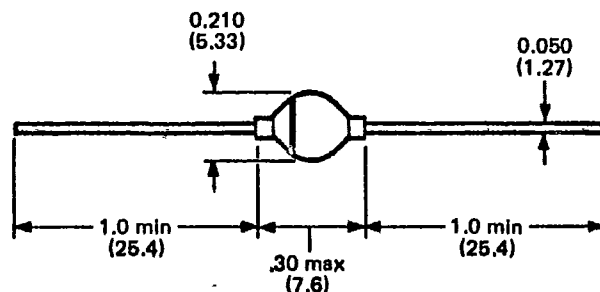
The CENTRAL SEMICONDUCTOR 1N5550 series types are silicon rectifiers mounted in a hermetically sealed, glass passivated package for general applications where high reliability is desired.

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL	1N5550	1N5551	1N5552	1N5553	1N5554	UNIT
Peak Repetitive Reverse Voltage	V_{RRM}	200	400	600	800	1000	V
DC Blocking Voltage	V_R	200	400	600	800	1000	V
RMS Reverse Voltage	$V_R(RMS)$	140	280	420	560	700	V
Average Forward Current ($T_A=55^\circ\text{C}$)	I_O			3.0			A
Peak Forward Surge Current	I_{FSM}			150			A
Operating and Storage Junction Temperature	T_J, T_{STG}			-65 TO +200			$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
I_R	V_R =Rated V_{RRM}		1.0	μA
I_R	V_R =Rated V_{RRM} , $T_A=100^\circ\text{C}$		75	μA
V_F	$I_F=3.0\text{A}$ (200V thru 600V)		1.0	V
V_F	$I_F=3.0\text{A}$ (800V thru 1000V)		1.1	V
BV_R	$I_R=50\mu\text{A}$ (1N5550)	240		V
BV_R	$I_R=50\mu\text{A}$ (1N5551)	460		V
BV_R	$I_R=50\mu\text{A}$ (1N5552)	660		V
BV_R	$I_R=50\mu\text{A}$ (1N5553)	880		V
BV_R	$I_R=50\mu\text{A}$ (1N5554)	1100		V
t_{rr}	$I_F=0.5\text{A}$, $I_R=1.0\text{A}$, Recov. to 0.25A (200V thru 600V)		2.0	μs
t_{rr}	$I_F=0.5\text{A}$, $I_R=1.0\text{A}$, Recov. to 0.25A (800V thru 1000V)		4.0	μs



DIMENSIONS IN INCHES (MILLIMETERS)